ALPHA & OMEGA SEMICONDUCTOR

AO4752

30V N-Channel AlphaMOS

General Description

- Latest Trench Power AlphaMOS (αMOS LV) technology
- Integrated Schottky Diode (SRFET)
- Very Low R_{DS}(on) at 4.5V_{GS}
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

Application

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

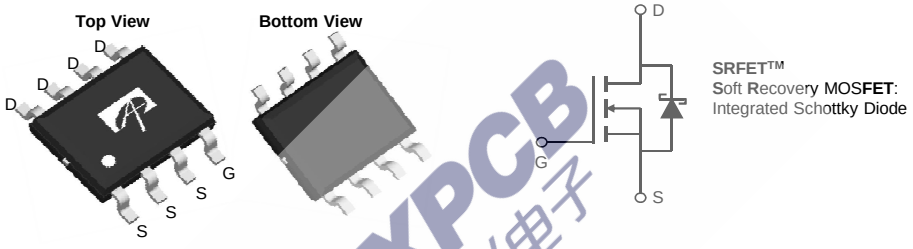
Product Summary

V_{DS}	30V
I_D (at V_{GS}=10V)	15A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 8.8mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 15.5mΩ

100% UIS Tested
100% R_g Tested

Green Product

SOIC-8



SRFET™
Soft Recovery MOSFET:
Integrated Schottky Diode

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	15	A
	T_A=70°C		12	
Pulsed Drain Current [C]		I_{DM}	102	
Avalanche Current [C]		I_{AS}	22	A
Avalanche energy L=0.05mH [C]		E_{AS}	12	mJ
V_{DS} Spike	100ns	V_{SPIKE}	36	V
Power Dissipation [B]	T_A=25°C	P_D	3.1	W
	T_A=70°C		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	31	40	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		59	75	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	16	24	°C/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=10mA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			0.5	mA
		T_J=55℃			100	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1.5	2	2.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=15A		7.2	8.8	mΩ
		T_J=125℃		10.2	12.5	
		V_{GS}=4.5V, I_D=10A		12.3	15.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=15A		71		S
V_{SD}	Diode Forward Voltage	I_S=0.2A,V_{GS}=0V		0.45	0.65	V
I_S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		605		pF
C_{oss}	Output Capacitance			275		pF
C_{rss}	Reverse Transfer Capacitance			36.5		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1	2	3	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=15A		11	15	nC
Q_g(4.5V)	Total Gate Charge			5.5	8	nC
Q_{gs}	Gate Source Charge			2		nC
Q_{gd}	Gate Drain Charge			2.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1Ω, R_{GEN}=3Ω		5		ns
t_r	Turn-On Rise Time			2.5		ns
$t_{D(off)}$	Turn-Off DelayTime			17		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=15A, dI/dt=500A/µs		11.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=15A, dI/dt=500A/µs		12.5		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

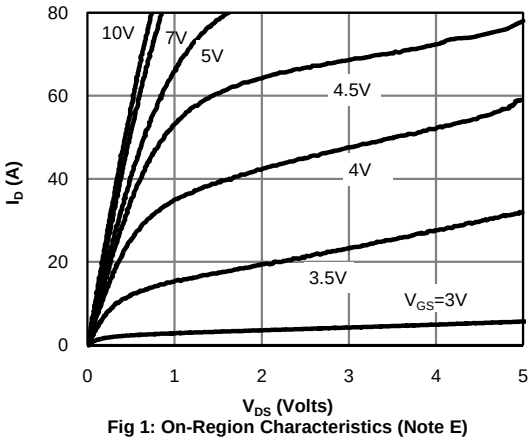


Fig 1: On-Region Characteristics (Note E)

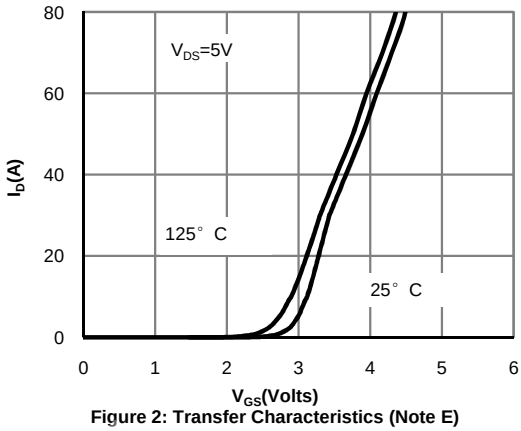


Figure 2: Transfer Characteristics (Note E)

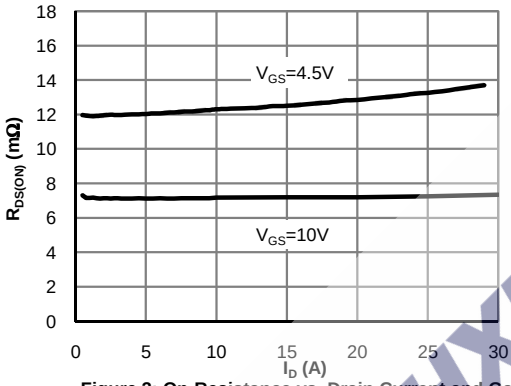


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

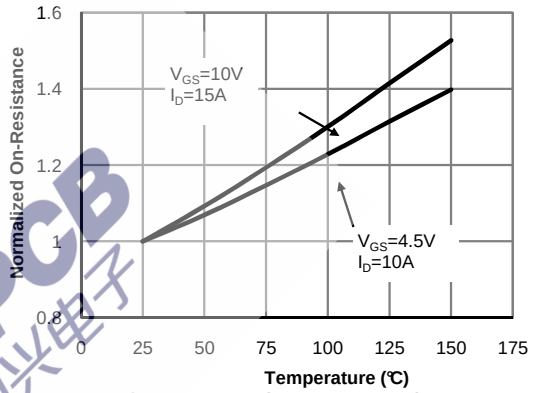


Figure 4: On-Resistance vs. Junction Temperature (Note E)

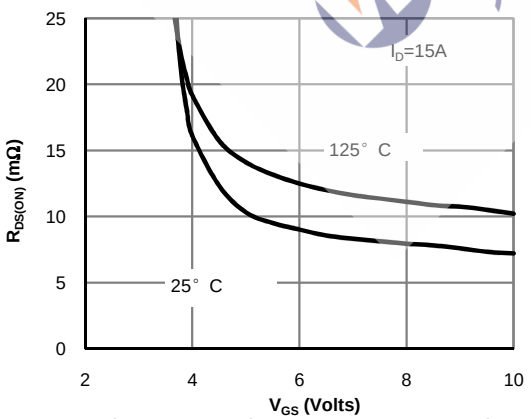


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

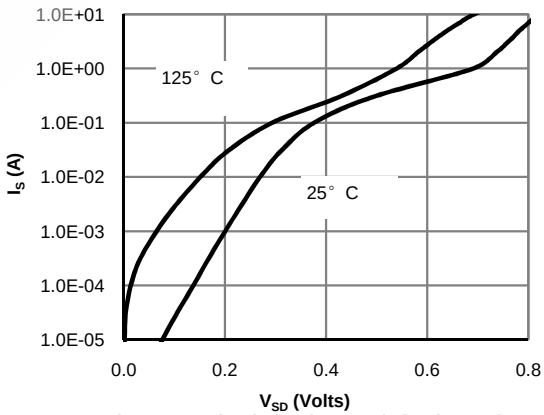


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

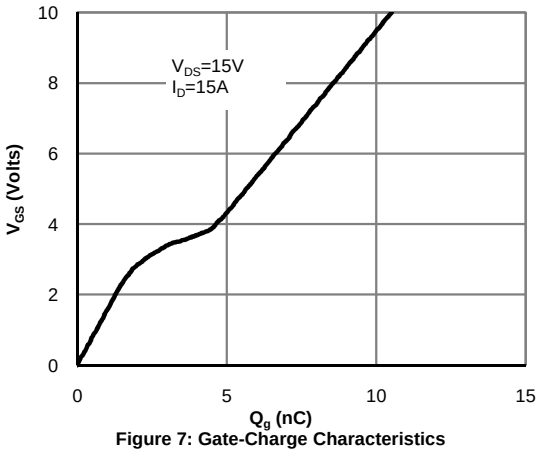


Figure 7: Gate-Charge Characteristics

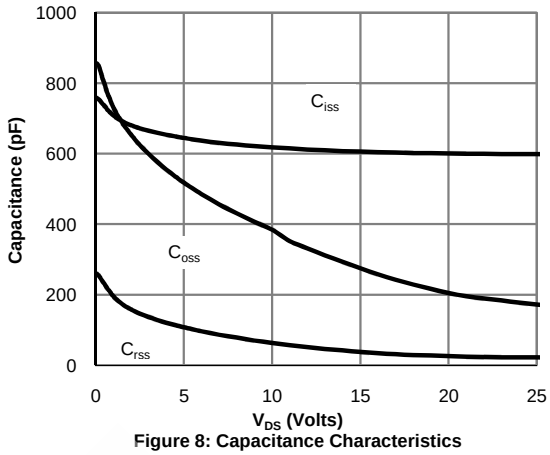


Figure 8: Capacitance Characteristics

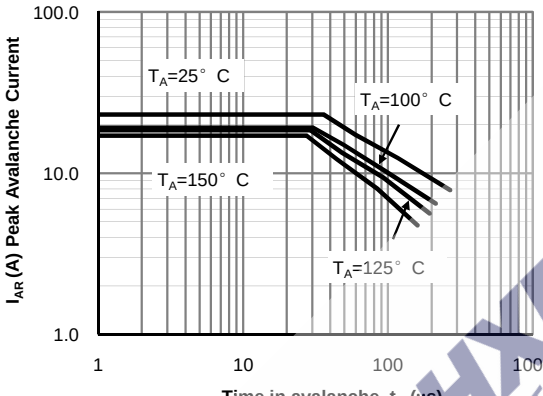


Figure 9: Single Pulse Avalanche capability (Note C)

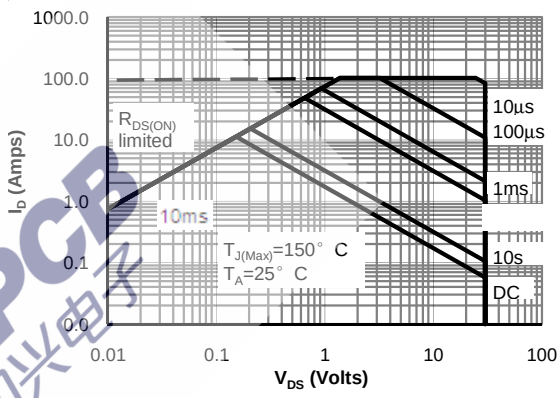


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

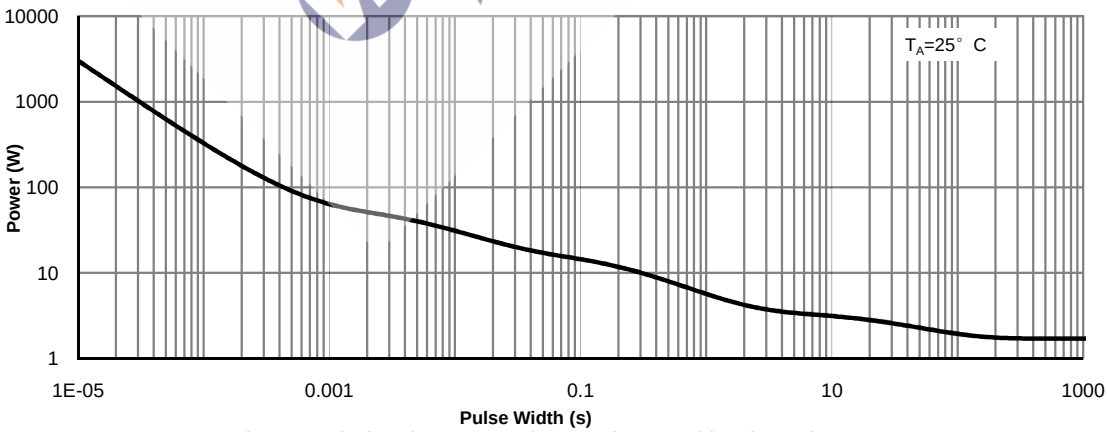


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

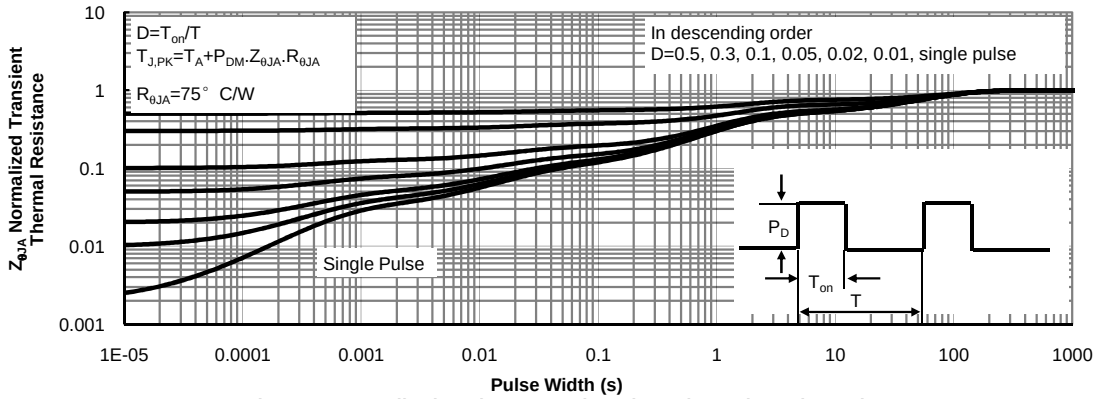
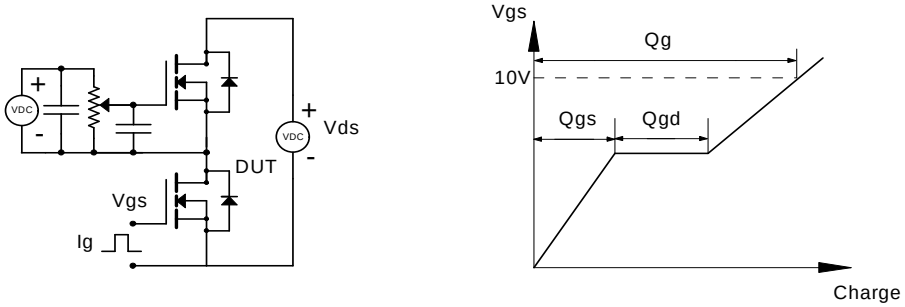
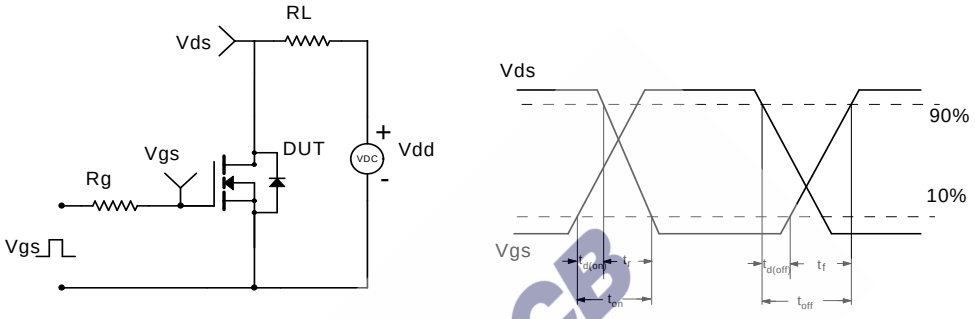


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

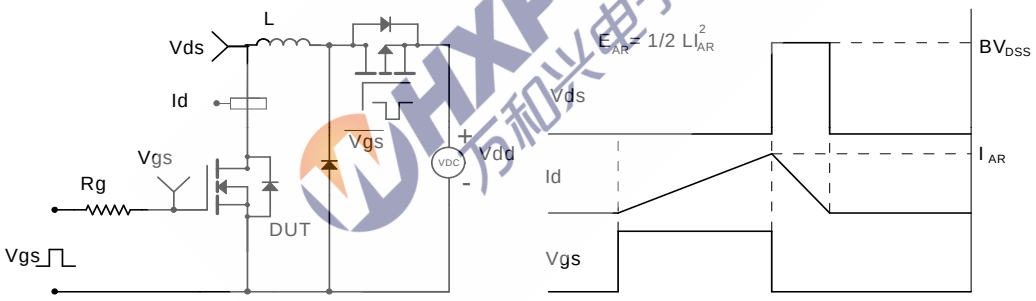
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms